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Customer No.: 31561 Application No.: 10/707,686

Docket No.: 11844-US-PA

AMENDMENTS

To the Claims:

Claim 1. (Currently amended) A chip package structure, comprising:

a carrier;

a chip, having an active surface with a plurality of bumps thereon, wherein the

chip is bonded and electrically connected to the carrier in a flip-chip bonding process;

a heat sink, set over the chip, wherein the heat sink has a surface area greater than

the chip and is unconnected to the carrier;

a plurality of standoff components, disposed over the heat sink and in a peripheral

area of the chip package structure, wherein the standoff components have a spherical

shape; and

an encapsulating material layer, filling a bonding gap between the chip and the

carrier and covering the heat sink and the carrier, wherein a top surface of the

encapsulating material layer is higher than that of the heat sink and the encapsulating

material layer is formed in a simultaneous molding process.

Claim 2. (Currently amended) The chip package structure of claim 1, wherein the

package further comprises a plurality of standoff-components set over the heat sink such

that a height of the standoff components above the heat sink is equal to a thickness of the

encapsulating material layer over the heat sink.

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Claim 3. (original) The chip package structure of claim 1, wherein the package further comprises a thermal conductive adhesive layer set between the chip and the heat sink.

Claim 4. (original) The chip package structure of claim 1, wherein the encapsulating material layer has a thermal conductivity greater than 1.2 W/m.K.

Claim 5. (original) The chip package structure of claim 1, wherein the encapsulating material comprises resin.

Claim 6. (original) The chip package structure of claim 1, wherein the heat sink is fabricated using a metallic material.

Claim 7. (original) The chip package structure of claim 1, wherein the package further comprises an array of solder balls attached to a carrier surface away from the chip.

Claim 8. (original) The chip package structure of claim 1, wherein the package further comprises a passive component set on and electrically connected to the carrier.

Claim 9. (original) The chip package structure of claim 1, wherein the carrier is selected from a group consisting of a packaging substrate or a lead frame.

Claim 10. (Currently amended) A chip package structure, comprising: a carrier;

a chipset, set over and electrically connected to the carrier, wherein the chipset comprises a plurality of chips, at least one of the chips is bonded to the carrier or another DEC-23-2005 FRI 15:34 FAX NO. P. 05/13

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chip in a flip-chip bonding process so that a flip-chip bonding gap is created;

a heat sink, set over the chipset, wherein the heat sink has a surface area greater

than the chipset and is unconnected to the carrier;

a plurality of standoff components, disposed over the heat sink and in a peripheral

area of the chip package structure, wherein the standoff components have a spherical

shape; and

an encapsulating material layer, filling the flip-chip bonding gap and covering the

heat sink and the carrier, wherein a top surface of the encapsulating material layer is

higher than that of the heat sink and the encapsulating material layer is formed in a

simultaneous molding process.

Claim 11. (Currently amended) The chip package structure of claim 10, wherein

the package further comprises a plurality of standoff components set over the heat sink

such that a height of the standoff components above the heat sink is equal to a thickness of

the encapsulating material layer over the heat sink.

Claim 12. (original) The chip package structure of claim 10, wherein the package

further comprises a thermal conductive adhesive layer set between the top surface of the

chipset and the heat sink.

Claim 13. (original) The chip package structure of claim 10, wherein the

encapsulating material layer has a thermal conductivity greater than 1.2 W/m.K.

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Claim 14. (original) The chip package structure of claim 10, wherein the chipset at least comprises:

a first chip, having a first active surface, wherein the first chip is attached to the

carrier such that the first active surface is positioned away from the carrier; and

a second chip, having a second active surface with a plurality of bumps thereon,

wherein the second active surface of the second chip is bonded and electrically connected

to the first chip in a flip-chip bonding process such that the bumps between the second

chip and the first chip set up a flip-chip bonding gap.

Claim 15. (original) The chip package structure of claim 14, wherein the chipset

further comprises a plurality of conductive wires with ends connected electrically to the

first chip and the carrier respectively.

Claim 16. (original) The chip package structure of claim 10, wherein the chipset at

least comprises:

a first chip, having an active surface with a plurality of first bumps thereon,

wherein the first active surface of the first chip is bonded and electrically connected to the

carrier in a flip-chip bonding process such that the first bumps between the first chip and

the carrier set up a flip-chip bonding gap;

a second chip, having a second active surface, wherein the second chip is attached

to the first chip such that the second active surface is positioned away from the first chip;

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and

a third chip, having a third active surface with a plurality of second bumps

thereon, wherein the third active surface of the third chip is bonded and electrically

connected to the second chip in a flip-chip bonding process such that the second bumps

between the third chip and the second chip set up another flip-chip bonding gap.

Claim 17. (original) The chip package structure of claim 16, wherein the chipset

further comprises a plurality of conductive wires with ends electrically connected to the

second chip and the carrier respectively.

Claim 18. (original) The chip package structure of claim 10, wherein the

encapsulating material comprises resin.

Claim 19. (original) The chip package structure of claim 10, wherein the heat sink

is fabricated using a metallic material.

Claim 20. (original) The chip package structure of claim 10, wherein the package

further comprises an array of solder balls attached to a carrier surface away from the

chipset.

Claim 21. (original) The chip package structure of claim 10, wherein the package

further comprises a passive component set on and electrically connected to the carrier.

Claim 22. (original) The chip package structure of claim 10, wherein the carrier is

selected from a group consisting of a packaging substrate or a lead frame.

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